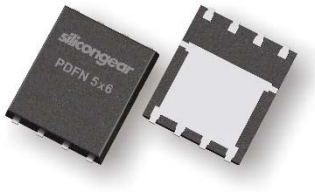
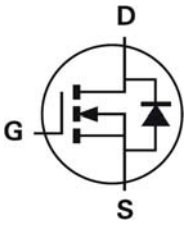
DG80N02HQ

DG-FET™ 80V N-Channel Power MOSFET

Parameter	Value	Unit
V_{DSS}	80	V
$R_{DS(ON)\ max.}$ V_{GS}=10V	6.7	mΩ
I_D	80	A
Q_g	30.35	nC
Q_{gd}	10.56	nC
Q_{SW}	14.32	nC

PDFN 5x6-8L





Features	Application
• Optimized for synchronous rectification Low Input Capacitance • Low Switching Charge • Low Miller Capacitance • Fully Characterized Capacitance and Avalanche • Pb-free lead plating; RoHS compliant	• BLDC Motor drive applications • Battery powered circuits • Half-bridge and full-bridge topologies • Synchronous rectifier applications • Resonant mode power supplies

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
DG80N02HQ	Halogen-Free	PDFN 5x6-8L	Q	Tape & Reel	2,500

Absolute Maximum Ratings (T_J=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous	T_C=25°C	I_D	80	A
	T_C=100°C		60	A
Drain Current-Pulsed Note 1	T_C=25°C	I_{DM}	350	A
Avalanche Current		I_{AR}	40	A
Single Pulse Avalanche Energy Note 3		E_{AS}	40	mJ
Maximum Power Dissipation	T_C=25°C	P_{tot}	96.2	W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Junction-to-Ambient **Note 2**	$R_{\theta JA}$	Steady State	-	-	50	°C/W
Thermal resistance, Junction-to-Case	$R_{\theta JC}$	Steady State	-	-	1.3	°C/W

Notes:

1. Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%.
2. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 in still air.
3. Limited by T_{Jmax}, starting T_J=25°C, L=50μH, R_g=50Ω, I_D=40A, V_{GS}=10V.

Electrical Characteristics (T_J=25°C unless otherwise noted)

STATIC CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_{DS}=10mA	80	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=64V, V_{GS}=0V, T_J=25°C	-	-	10	µA
		V_{DS}=64V, V_{GS}=0V, T_J=125°C	-	-	100	µA
Gate-Body Leakage	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA

STATIC CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_{DS}=250µA	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_{DS}=20A	-	-	6.7	mΩ
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz	-	0.6	1	Ω
Forward Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|$ $R_{DS(ON)\ m,ax}$, I_{DS}=40A	-	70	-	S

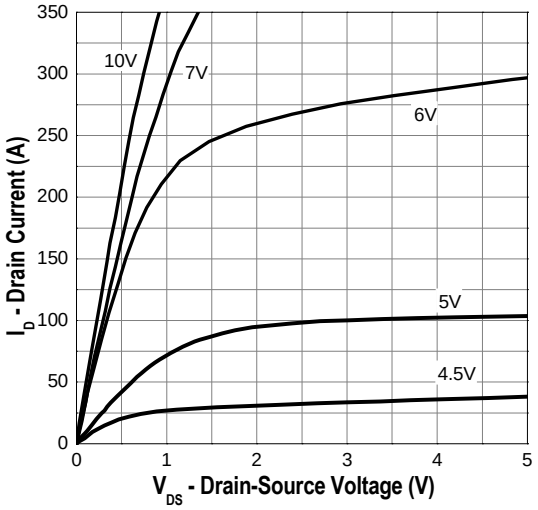
DYNAMIC CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Input Capacitance	C_{iss}	V_{DS}=40V, V_{GS}=0V, f=1MHz	-	1456	-	pF
Output Capacitance	C_{oss}	V_{DS}=40V, V_{GS}=0V, f=1MHz	-	435	-	pF
Reverse Transfer Capacitance	C_{rss}	V_{DS}=40V, V_{GS}=0V, f=1MHz	-	21	-	pF
Turn-On Delay Time	$T_{d(on)}$	V_{DS}=40V, V_{GS}=10V, I_{DS}=40A, R_{GEN}=3.6Ω	-	9.6	-	ns
Rise Time	t_r	V_{DS}=40V, V_{GS}=10V, I_{DS}=40A, R_{GEN}=3.6Ω	-	24.6	-	ns
Turn-Off Delay Time	$T_{d(off)}$	V_{DS}=40V, V_{GS}=10V, I_{DS}=40A, R_{GEN}=3.6Ω	-	21	-	ns
Fall Time	t_f	V_{DS}=40V, V_{GS}=10V, I_{DS}=40A, R_{GEN}=3.6Ω	-	31	-	ns

GATE CHARGE CHARACTERISTICS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Gate to Source Gate Charge	Q_{gs}	V_{DD}=40V, I_D=40A, V_{GS}=0 to 10V	-	8.51	-	nC
Gate charge at threshold	$Q_{g(th)}$	V_{DD}=40V, I_D=40A, V_{GS}=0 to 10V	-	4.75	-	nC
Gate to Drain Charge	Q_{gd}	V_{DD}=40V, I_D=40A, V_{GS}=0 to 10V	-	10.56	-	nC
Switching charge	Q_{SW}	V_{DD}=40V, I_D=40A, V_{GS}=0 to 10V	-	14.32	-	nC
Gate charge total	Q_g	V_{DD}=40V, I_D=40A, V_{GS}=0 to 10V	-	30.35	-	nC
Gate plateau voltage	$V_{plateau}$	V_{DD}=40V, I_D=40A, V_{GS}=0 to 10V	-	5.27	-	V
Gate charge total, sync. FET (Q_g- Q_{gd})	$Q_{g(sync)}$	V_{DS}=0.1V, V_{GS}=0 to 10V	-	19.79	-	nC

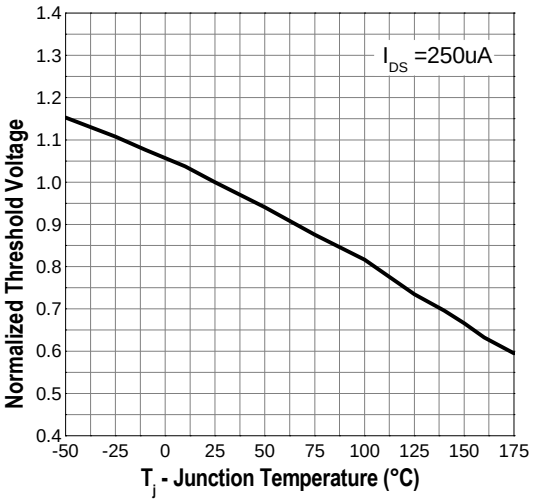
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	**Symbol**	**Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Diode continuous forward current (Body Diode)	I_S	T_C=25°C	-	-	80	A
Diode pulse current (Body Diode)	I_{SM}	T_C=25°C	-	-	350	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=40A	-	-	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	V_{DD}=40V, I_F=40A, di/dt=100A/µs	-	31	-	ns
		V_{DD}=40V, I_F=40A, di/dt=200A/µs	-	22	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}	V_{DD}=40V, I_F=40A, di/dt=100A/µs	-	30	-	nC
		V_{DD}=40V, I_F=40A, di/dt=200A/µs	-	47	-	nC

Typical Operating Characteristics

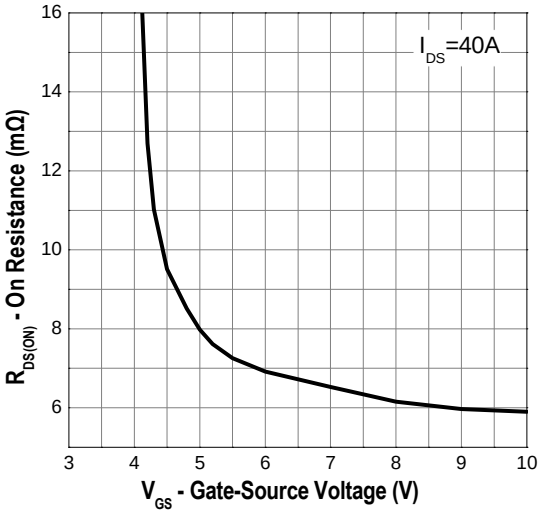
Output Characteristics



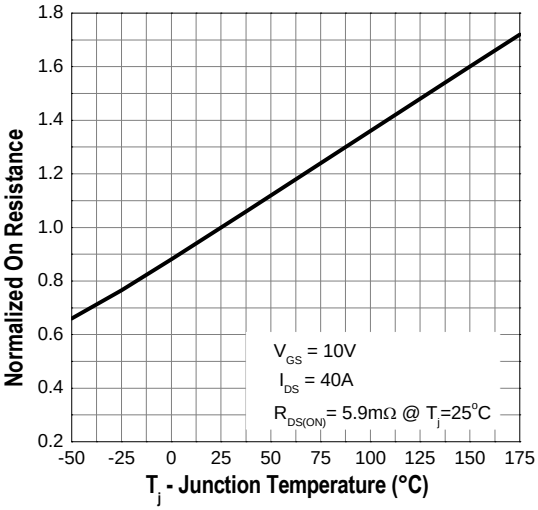
Gate Threshold Voltage



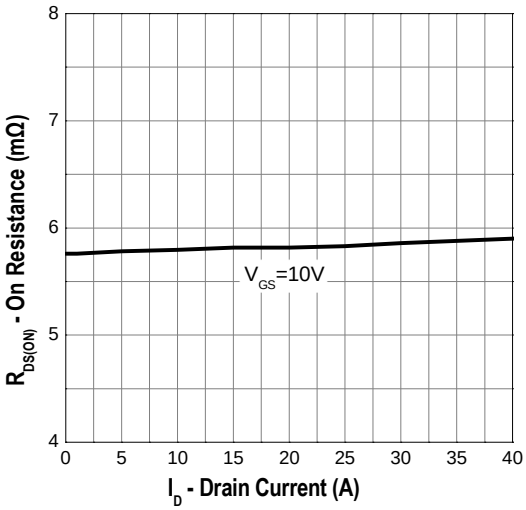
Gate-Source On Resistance



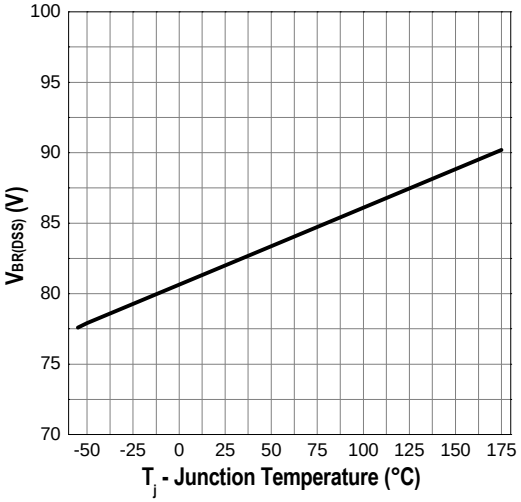
Drain-Source On Resistance



Drain-Source On Resistance

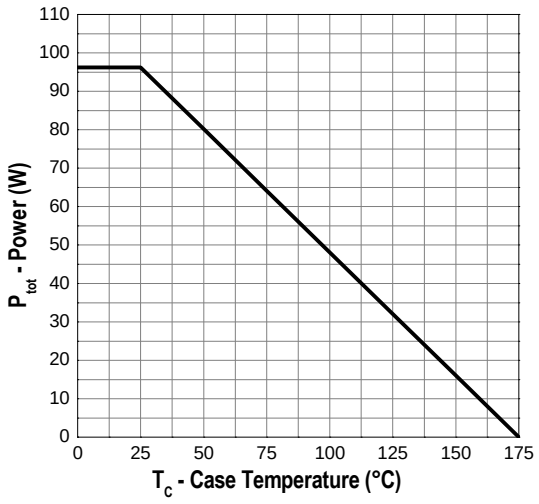


Drain-source Breakdown Voltage

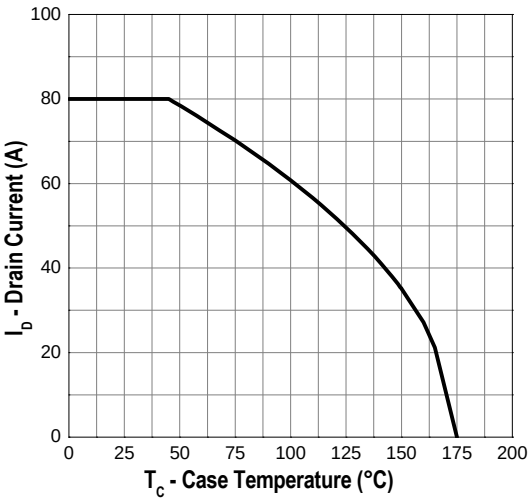


Typical Operating Characteristics (Cont.)

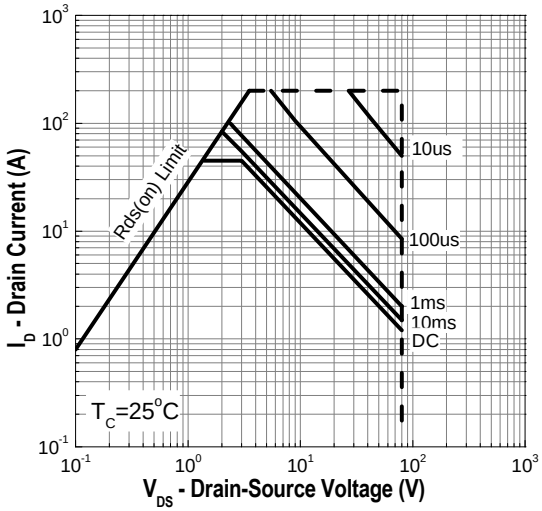
Power Dissipation



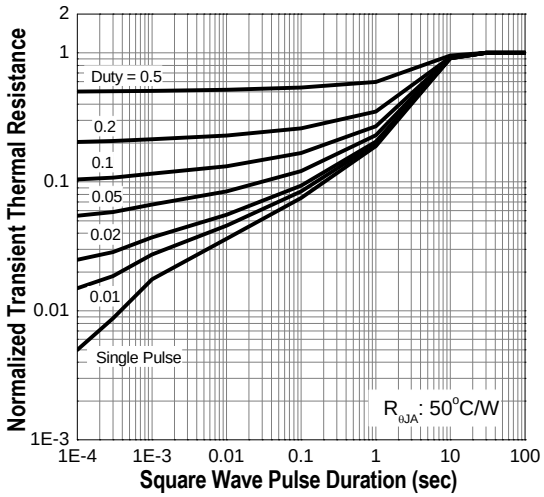
Drain Current



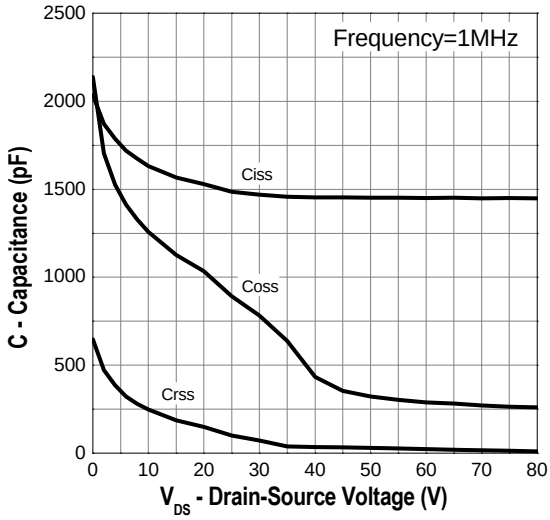
Safe Operation Area



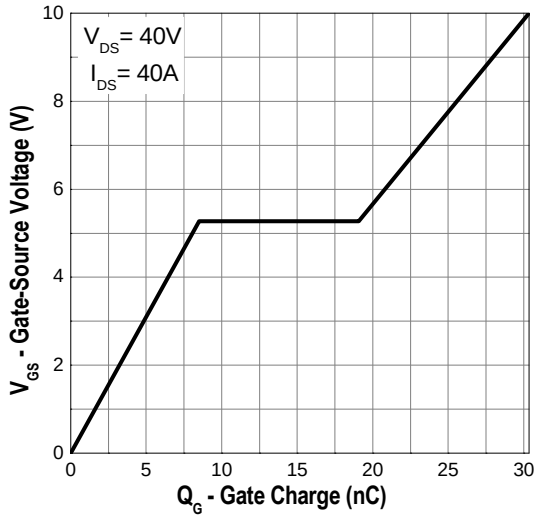
Transient Thermal Impedance



Capacitance



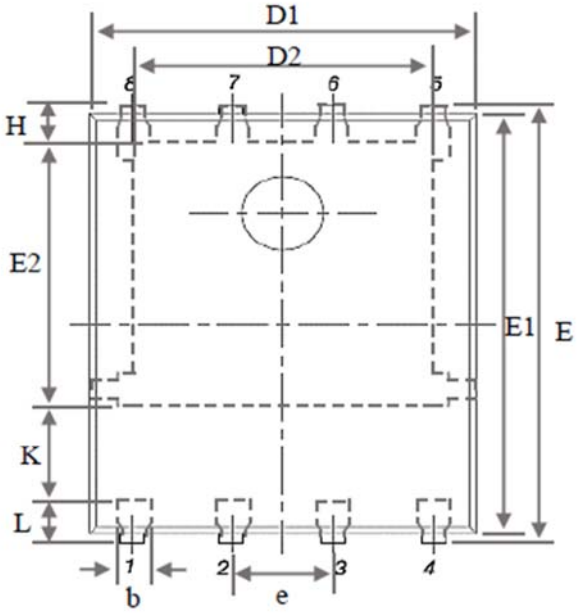
Gate Charge

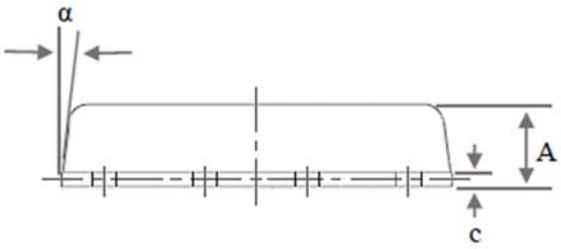


Marking Information

PDFN 5x6-8L (Q)	Marking Rule
Laser Marking  	Line 1：Device DG80N02HQ Line 2：Date Code YYMMXXX YY：Year Code MM：Month Code XXX：Serial Number

Package of Dimension



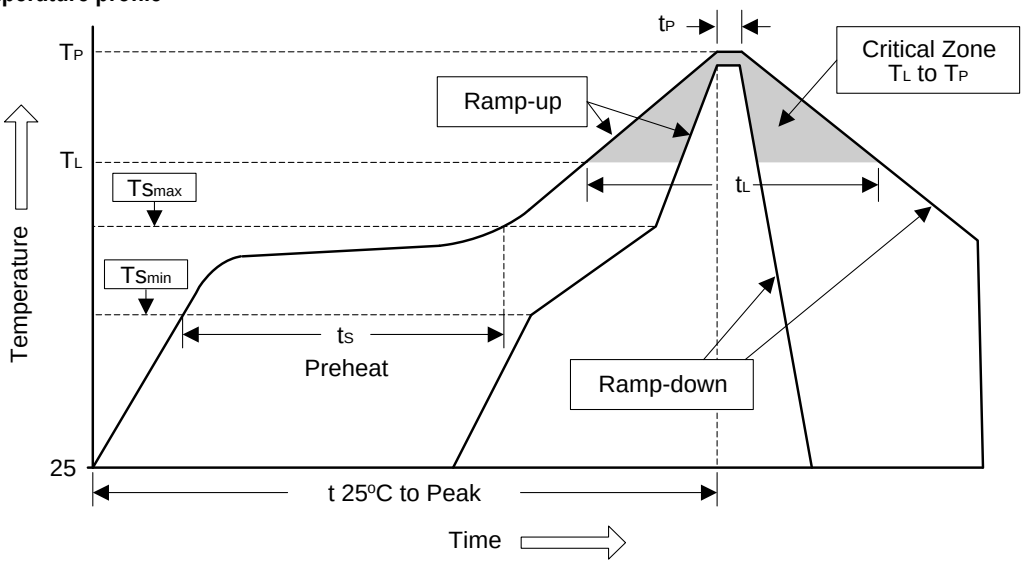


Symbol	Min	Nor	Max
A	0.90	1.04	1.17
b	0.33	0.42	0.51
C	0.06	0.20	0.35
D1	4.80	5.10	5.40
D2	3.61	3.96	4.31
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
e	1.27 BSC		
H	0.38	0.50	0.61
L	0.38	0.55	0.71
L1	0.05	0.15	0.25

Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat - Temperature Min (Ts_{min}) - Temperature Max (Ts_{max}) - Time (min to max) (ts)	 100°C 150°C 60 to 120 sec	 150°C 200°C 60 to 180 sec
Tsmax to T_L - Ramp-up Rate	 <3°C/sec	 <3°C/sec
Time maintained above: - Temperature (T_L) - Time (t_L)	 183°C 60 to 150 sec	 217°C 60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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